

MOSFET N-CH 120V 120A TO220-3

Manufacturers [Infineon Technologies Corporation](#)

Package/Case TO-220

Product Type Transistors

RoHS

Lifecycle



Images are for reference only

Please submit RFQ for IPP041N12N3G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPP041N12N3G is a power MOSFET (Metal Oxide Semiconductor Field-Effect Transistor) manufactured by Infineon Technologies.

Features

It has a drain-source voltage rating of 120V and a continuous drain current rating of 80A.

The on-resistance of this MOSFET is very low (typically 4.1 milliohms), which means that it has low power dissipation and high efficiency.

It has a fast switching speed, which makes it suitable for high-frequency switching applications.

It has a rugged design, which makes it suitable for harsh environments.

Application

Switched-mode power supplies (SMPS)

DC-DC converters

Motor control

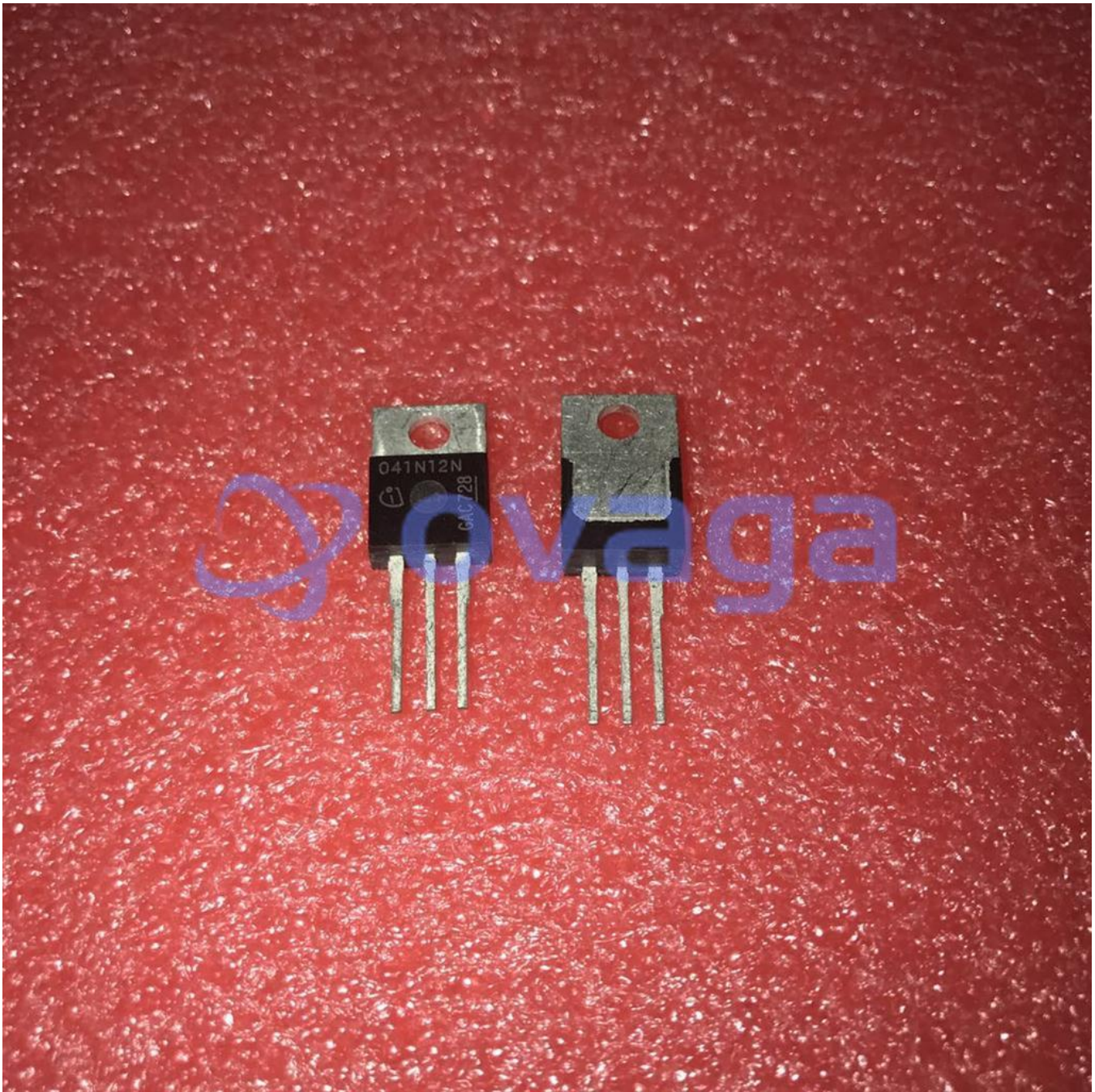
Solar inverters

Uninterruptible power supplies (UPS)

Welding equipment

Electric vehicles (EVs)

Battery management systems (BMS)



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



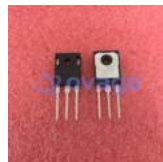
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

Infineon Technologies Corporation
TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation
PG-TO252-3



[IPD180N10N3G](#)

Infineon Technologies Corporation
TO-252



[IPP60R074C6](#)

Infineon Technologies Corporation
TO-220-3



[IPD70R1K4P7S](#)

Infineon Technologies Corporation
TO252-3